

CLAIMS

1., A method of testing a semiconductor storage device, comprising the steps of:

5 setting a plurality of test patterns in a tester for testing semiconductor storage devices;

 applying different test patterns to respective semiconductor storage devices connected to said tester; and

10 determining whether or not results of the tested semiconductor storage devices fall within a predetermined tolerance.

2. The method of testing a semiconductor storage device according to claim 1, wherein the number of defective bit lines of said tested semiconductor storage device having exceeded a
15 tolerance is compared with the number of redundant lines on the basis of a test result output, thereby determining semiconductor storage devices which can be restored through use of redundant lines.

3. The method of testing a semiconductor storage device
20 according to claim 1, wherein the number of defective column lines of said tested semiconductor storage device having exceeded a tolerance is compared with the number of redundant lines on the basis of a test result output, thereby determining semiconductor storage devices which can be restored through use
25 of redundant lines.

4. The method of testing a semiconductor storage device according to claim 1, wherein a test is performed several times

while a test pattern is changed.

5 5. The method of testing a semiconductor storage device according to claim 1, wherein, when said tested semiconductor storage devices are non-volatile, the devices are subjected to writing and erasure tests.

6. The method of testing a semiconductor storage device according to claim 1, wherein a test pattern is made by combination of a voltage, a time, and a signal.

10000160-120401